

## ABSTRACT

A semiconductor device of the present invention includes a MISFET provided in an element formation region **Re** of a semiconductor substrate **11** and a trench isolation **13**.  
5 surrounding the sides of the element formation region **Re**. An oxygen-passage-suppression film **23** is provided from the top of the trench isolation **13** to the top of a portion of the element formation region **Re** adjacent to the trench isolation **13**. The oxygen-passage-suppression film **23** is made of a silicon nitride film or the like through which oxygen is less likely to permeate. Therefore, since it becomes hard that  
10 the upper edge of the element formation region **Re** of the semiconductor substrate **11** is oxidized, an expansion of the volume of the upper edge is suppressed, thereby reducing a stress.